

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

Shunpei YAMAZAKI et al.

Serial No. 09/334,646

Filed: June 17, 1999

For: SEMICONDUCTOR DEVICE AND  
FABRICATION METHOD  
THEREOF

) Group Art Unit: 2811

) Examiner: S. Hu

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on: 1-13-04.

Adel M. Stamer

REQUEST FOR ACKNOWLEDGMENT OF  
INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

The Applicants note with appreciation the consideration of the Information Disclosure Statements filed on May 30, 2000, October 4, 2000, September 26, 2001, March 13, 2002, and April 30, 2003. The Applicants also note the partial consideration of the IDS filed on June 17, 1999, a partially initialed copy of which was included with the Official Action dated December 27, 1999. The following references were not considered by the Examiner: (1) C. Hayzelden et al., "In Situ Transmission Electron Microscopy Studies of Silicide-Mediated Crystallization of Amorphous Silicon" (3 pages); (2) A.V. Dvurechenskii et al., "Transport Phenomena in Amorphous Silicon Doped by Ion Implantation of 3d Metals," Akademikian Lavrentev Prospekt 13, 630090 Novosibirsk 90, USSR, pp. 635-640; and (3) R. Kakkad et al., "Low Temperature Selective Crystallization of Amorphous Silicon," Journal of Non-Crystalline Solids, 115, 1989, pp. 66-68.

In response to the Applicants' request in the *Amendment* filed June 11, 2003, the Examiner notes in the Official Action dated August 20, 2003, that copies of the Hayzelden and Kakkad articles were not found in the parent application Serial No. 08/513,090. However, the Examiner has not indicated whether parent application Serial No. 08/938,310 was reviewed. Also, it is unclear from the record whether the Examiner has a

copy of the Dvurechenskii article. It does not appear that the Dvurechenskii article has been considered.

The Official Action asserts that the IDS fails to comply with 37 CFR 1.98(a)(2). The Applicants respectfully disagree. Please note that the present application is a Division (DIV) of copending applications Serial No. 08/513,090, filed August 9, 1995, now U.S. Patent No. 5,731,613, and Serial No. 08/938,310, filed September 26, 1997, now U.S. Patent No. 5,959,313. Under 37 CFR 1.98(d)(1), the Applicants are permitted to rely on an earlier submission of prior art in a parent application if the "earlier application is properly identified in the information disclosure statement and is relied on for an earlier effective filing date under 35 U.S.C. 120." The '090 and '310 applications are properly identified in the IDS, in the *Utility Patent Application Transmittal*, and in amendment to the specification in the *Preliminary Amendment*, all of which were filed June 17, 1999. Therefore, the IDS filed June 17, 1999, fully complies with 37 CFR 1.98, and all the references cited therein should be considered.

In response and as a courtesy to the Examiner, the Applicants have provided herewith copies of the Hayzelden article, the Dvurechenskii article, the Kakkad article, the IDS and Form PTO-1449 filed June 17, 1999, and the receipt cards noting the filing of the IDS and Form PTO-1449. It is respectfully requested that the Hayzelden article, the Dvurechenskii article, and the Kakkad article cited in this IDS be considered by the Examiner and an initialed Form 1449 returned evidencing such consideration.

Should the Examiner believe that anything further would be desirable in considering the IDS filed June 17, 1999, or to place this application in better condition for allowance, the Examiner is invited to contact the Applicants' undersigned attorney at the telephone number listed below.

Respectfully submitted,

  
Eric J. Robinson  
Reg. No. 38,285

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(571) 434-6789



- 1 -

Docket: 0756-1984

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT Application of )  
Shunpei YAMAZAKI et al. )  
Based On Serial No. 08/938,310 ) Art Unit: 2811  
Which Was Filed: September 26, 1997 ) Examiner: F. Abraham  
For: SEMICONDUCTOR DEVICE AND )  
FABRICATION METHOD )  
THEREOF ) Date: June 17, 1999

INFORMATION DISCLOSURE STATEMENT

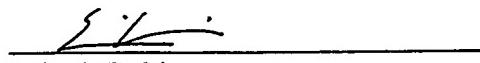
Honorable Assistant Commissioner for Patents  
Washington, D.C. 20231

Sir:

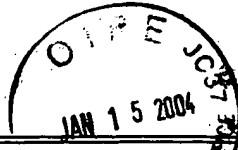
In accordance with the provisions of 37 C.F.R. 1.56 and 37 C.F.R. 1.97-1.99, it is requested that the references listed on the attached Form PTO-1449 be made of record in the above-identified application.

The references listed on the attached Form PTO-1449 were cited in parent application Serial No. 08/938,310 filed September 26, 1997, and its predecessor application Serial No. 08/513,090.

Respectfully submitted,

  
Eric J. Robinson  
Registration No. 38,285

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Sheet 1 of 1

Form PTO-1449  
(Rev. 8-83)U.S. Department of Commerce  
Patent and Trademark Office

## INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

Attorney Docket No. 0756-1984

Serial No. Not Yet Assigned

Applicant: Shunpei YAMAZAKI et al.

Filing Date: June 17, 1999

Group: 2811

## U.S. PATENT DOCUMENTS

Examiner Initial		Patent Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
		5,581,092	12/03/96	Takemura			
		5,500,538	03/19/96	Yamazaki et al.			
		5,147,826	09/15/92	Liu et al.			
		5,275,851	01/04/94	Fonash et al.			
		5,731,613	03/24/98	Yamazaki	257	350	
		5,581,092	12/03/96	Takemura	257	192	

## FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Clas s	Subcl ass	Translation Yes No

## OTHER DOCUMENTS (Including Author, Title, Relevant Pages, Date, Place of Publication)

	C. Hayzelden et al., "In Situ Transmission Electron Microscopy Studies of Silicide-Mediated Crystallization of Amorphous Silicon" (3 pages)
	A.V. Dvurechenskii et al., "Transport Phenomena in Amorphous Silicon Doped by Ion Implantation of 3d Metals", <u>Akademikian Lavrentev Prospekt</u> 13, 630090 Novosibirsk 90, USSR, pp. 635-640.
	T. Hempel et al., "Needle-Like Crystallization of Ni Doped Amorphous Silicon Thin Films", <u>Solid State Communications</u> , Vol. 85, No. 11, pp. 921-924, 1993.
	R. Kakkad et al., "Crystallized Si films by low-temperature rapid thermal annealing of amorphous silicon," <u>J.Appl. Phys.</u> , 65(5), March 1, 1989, pp. 2069-72.
	G. Liu et al., "Polycrystalline silicon thin film transistors on Corning 7059 glass substrates using short time, low-temperature processing," <u>Appl. Phys. Lett.</u> 62(20), May 17, 1993, pp. 2554-2556.
	G. Liu et al., "Selective area crystallization of amorphous silicon films by low-temperature rapid thermal annealing," <u>Appl. Phys. Lett.</u> 55(7), August 14, 1989, pp. 660-662.
	R. Kakkad et al., "Low Temperature Selectiv Crystallization of Amorphous Silicon," <u>Journal of Non-Crystalline Solids</u> , 115, 1989, pp. 66-68.

Examiner

Date Considered

\*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.